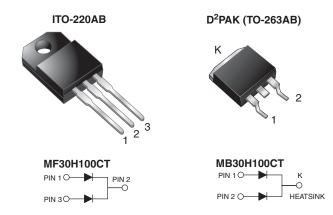


Vishay General Semiconductor

## **Dual Common Cathode High Voltage Schottky Rectifier**

High Barrier Technology for Improved High Temperature Performance



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	15 A x 2			
V <sub>RRM</sub>	100 V			
I <sub>FSM</sub>	275 A			
V <sub>F</sub>	0.67 V			
I <sub>R</sub>	5.0 μA			
T <sub>J</sub> max.	175 °C			
Package	ITO-220AB, D <sup>2</sup> PAK (TO-263AB)			
Circuit configuration	Common cathode			

#### **FEATURES**

- Power pack
- · Guardring for overvoltage protection
- Low power loss, high efficiency
- Low forward voltage drop
- Low leakage current
- High forward surge capability
- High frequency operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for D<sup>2</sup>PAK (TO-263AB) package)
- Solder bath temperature 275 °C maximum, 10 s, per JESD 22-B106 (for ITO-220AB package)
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912"><u>www.vishav.com/doc?99912</u></a>

#### TYPICAL APPLICATIONS

For use in high frequency rectifier of switching mode power supplies, freewheeling diodes, DC/DC converters, and polarity protection application.

### **MECHANICAL DATA**

Case: ITO-220AB, D2PAK (TO-263AB)

Molding compound meets UL 94 V-0 flammability rating Base P/NHE3\_X - RoHS-compliant, AEC-Q101 qualified ("\_X" denotes revision code e.g. A, B, .....)

Terminals: matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102

HE3 suffix meets JESD 201 class 2 whisker test

Polarity: as marked

Mounting Torque: 10 in-lbs maximum

PARAMETER		SYMBOL	MB30H100CT	UNIT		
Maximum repetitive peak reverse voltage		V <sub>RRM</sub>	100			
Working peak reverse voltage		V <sub>RWM</sub>	100	V		
Maximum DC blocking voltage		V <sub>DC</sub>	100			
Maximum average forward rectified current (fig.1)	total device	,	30			
	per diode	I <sub>F(AV)</sub>	15			
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode		I <sub>FSM</sub>	275	A		
Peak repetitive reverse surge current per diode at $t_p$ = 2.0 $\mu$ s, 1 kHz		I <sub>RRM</sub>	1.0			
Voltage rate of change (rated V <sub>R</sub> )		dV/dt	10 000	V/µs		
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>STG</sub>	-65 to +175	°C		
Isolation voltage (ITO-220AB only) from terminal to heat sink t = 1 min		V <sub>AC</sub>	1500	V		



# MB30H100CT, MF30H100CT

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<b>ELECTRICAL CHARACTERISTICS</b> (T <sub>C</sub> = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUE	UNIT
Maximum instantaneous forward voltage per diode	V <sub>F</sub> (1)	I <sub>F</sub> = 15 A	T <sub>J</sub> = 25 °C	0.82	V
		I <sub>F</sub> = 15 A	T <sub>J</sub> = 125 °C	0.67	
		I <sub>F</sub> = 30 A	T <sub>J</sub> = 25 °C	0.93	
		I <sub>F</sub> = 30 A	T <sub>J</sub> = 125 °C	0.80	
Maximum reverse current per diode	I <sub>R</sub> <sup>(2)</sup>	Rated V <sub>R</sub>	T <sub>J</sub> = 25 °C	5.0	μΑ
			T <sub>J</sub> = 125 °C	6.0	mA

#### Note

 $^{(1)}\,$  Pulse test: 300  $\mu s$  pulse width, 1 % duty cycle

(2) Pulse test: Pulse width, ≤ 40 ms

THERMAL CHARACTERISTICS (T <sub>C</sub> = 25 °C unless otherwise noted)				
PARAMETER	SYMBOL	МВ	MF	UNIT
Typical thermal resistance per diode	$R_{ heta JC}$	1.9	4.6	°C/W

ORDERING IN	FORMATION (Example)				
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
ITO-220AB	MF30H100CTHE3_B/P (1)	1.99	Р	50/tube	Tube
TO-263AB	MB30H100CTHE3_B/P (1)	1.35	Р	50/tube	Tube
TO-263AB	MB30H100CTHE3_B/I (1)	1.35	I	800/reel	Tape and reel

### Note

(1) AEC-Q101 qualified

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### **RATINGS AND CHARACTERISTICS CURVES** ( $T_C = 25$ °C unless otherwise noted)

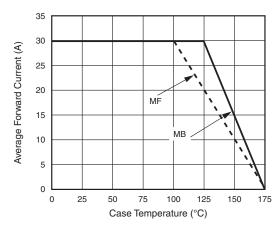


Fig. 1 - Forward Derating Curve Per Diode

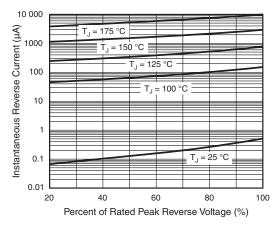


Fig. 4 - Typical Reverse Characteristics Per Diode

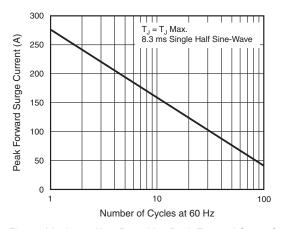


Fig. 2 - Maximum Non-Repetitive Peak Forward Surge Current Per Diode

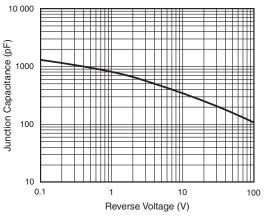


Fig. 5 - Typical Junction Capacitance Per Diode

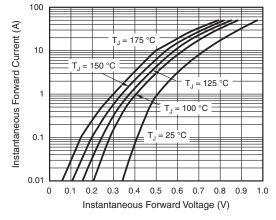


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

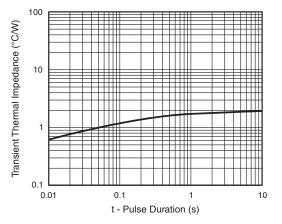
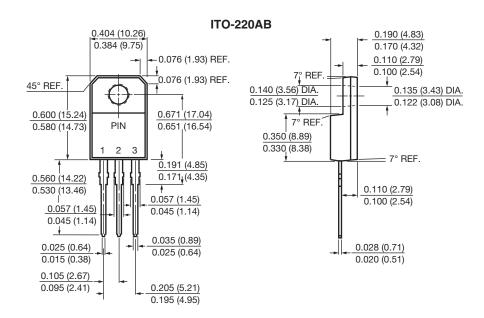


Fig. 6 - Typical Transient Thermal Impedance Per Diode

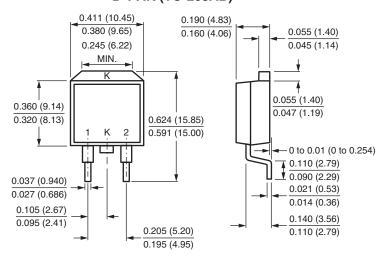


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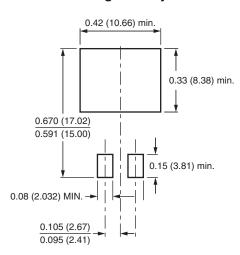
### PACKAGE OUTLINE DIMENSIONS in inches (millimeters)



### D<sup>2</sup>PAK (TO-263AB)



#### **Mounting Pad Layout**



### **Legal Disclaimer Notice**



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